imall

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BCX68...

NPN Silicon AF Transistors

- For general AF applications
- High collector current
- High current gain
- Low collector-emitter saturation voltage
- Complementary type: BCX69 (PNP)
- Pb-free (RoHS compliant) package
- Qualified according AEC Q101



≤ 1	RoHS
Qualified	

|--|--|

Туре	Marking	Pin Configuration			Package
BCX68-10	СВ	1=B	2=C	3=E	SOT89
BCX68-16	CC	1=B	2=C	3=E	SOT89
BCX68-25	CD	1=B	2=C	3=E	SOT89

Maximum Ratings

Parameter	Symbol	Value	Unit	
Collector-emitter voltage	V _{CEO}	20	V	
Collector-base voltage	V _{CBO}	25		
Emitter-base voltage	V _{EBO}	5		
Collector current	I _C	1	А	
Peak collector current, $t_p \leq 10 \text{ ms}$	I _{CM}	2		
Base current	/ _B	100	mA	
Peak base current	/ _{BM}	200		
Total power dissipation-	P _{tot}	3	W	
<i>T</i> _S ≤ 114 °C				
Junction temperature	Ti	150	°C	
Storage temperature	T _{stg}	-65 150		
Thermal Resistance				

Parameter	Symbol	Value	Unit			
Junction - soldering point ¹⁾	R _{thJS}	≤ 12	K/W			

¹For calculation of R_{thJA} please refer to Application Note AN077 (Thermal Resistance Calculation)



Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics			1	r	1
Collector-emitter breakdown voltage	V _{(BR)CEO}	20	-	-	V
I _C = 30 mA, I _B = 0					
Collector-base breakdown voltage	V _{(BR)CBO}	25	-	-	
/ _C = 10 μA, / _E = 0					
Emitter-base breakdown voltage	V _{(BR)EBO}	5	-	-	
/ _E = 1 μA, / _C = 0	, , ,				
Collector-base cutoff current	I _{CBO}				μA
$V_{\rm CB} = 25 \text{ V}, I_{\rm E} = 0$		-	-	0.1	
V _{CB} = 25 V, <i>I</i> _E = 0 , <i>T</i> _A = 150 °C		-	-	100	
DC current gain ¹⁾	h _{FE}				-
/ _C = 5 mA, V _{CE} = 10 V		50	-	-	
<i>I</i> _C = 500 mA, <i>V</i> _{CE} = 1 V, BCX68-10		85	100	160	
<i>I</i> _C = 500 mA, <i>V</i> _{CE} = 1 V, BCX68-16		100	160	250	
<i>I</i> _C = 500 mA, <i>V</i> _{CE} = 1 V, BCX68-25		160	250	375	
$I_{\rm C}$ = 1 A, $V_{\rm CE}$ = 1 V		60	-	-	
Collector-emitter saturation voltage1)	V _{CEsat}	-	-	0.5	V
<i>I</i> _C = 1 A, <i>I</i> _B = 100 mA					
Base-emitter voltage ¹⁾	V _{BE(ON)}]
I _C = 5 mA, V _{CE} = 10 V	, ,	-	0.6	-	
I _C = 1 A, V _{CE} = 1 V		-	-	1	
AC Characteristics					

Electrical Characteristics at $T_{\Delta} = 25^{\circ}$ C, unless otherwise specified

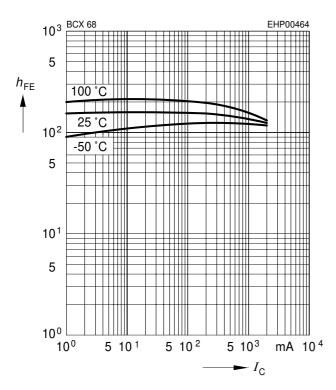
Transition frequency	f _T	-	100	-	MHz
<i>I</i> _C = 100 mA, <i>V</i> _{CE} = 5 V, <i>f</i> = 20 MHz					

¹Pulse test: t < 300µs; D < 2%

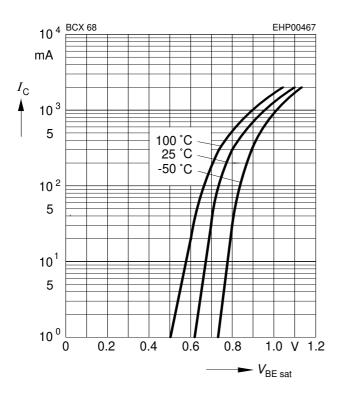


DC current gain $h_{\text{FE}} = f(I_{\text{C}})$

 $V_{CE} = 1 V$

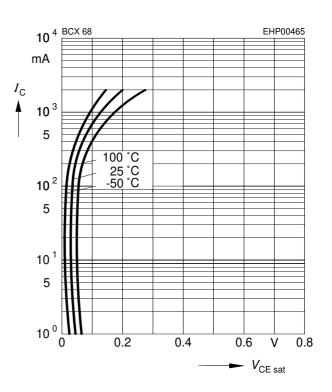


Base-emitter saturation voltage $I_{\rm C} = f(V_{\rm BEsat}), h_{\rm FE} = 10$

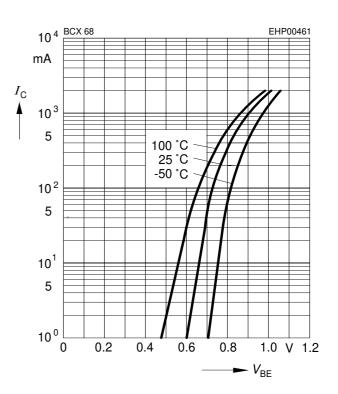


Collector-emitter saturation voltage

 $I_{\rm C} = f(V_{\rm CEsat}), h_{\rm FE} = 10$



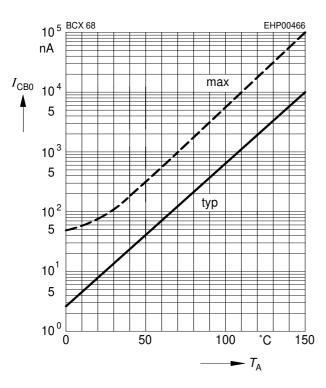
Collector current $I_{\rm C} = f(V_{\rm BE})$ $V_{\rm CE} = 1V$



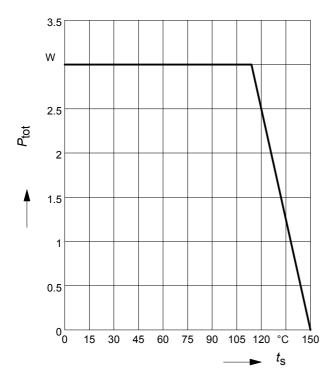


Collector cutoff current $I_{CBO} = f(T_A)$

 $V_{\rm CB}$ = 25 V

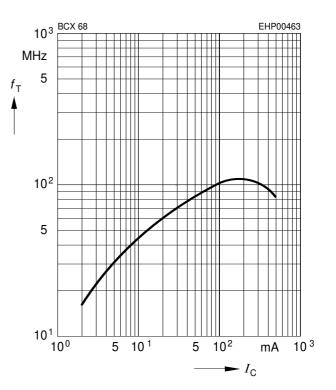


Total power dissipation $P_{tot} = f(T_S)$

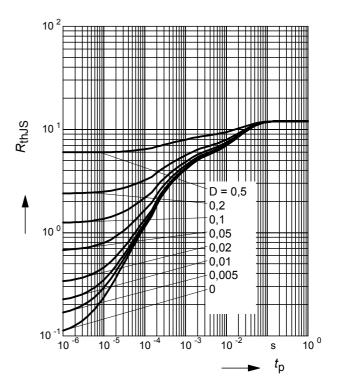


Transition frequency $f_{\rm T} = f(I_{\rm C})$

 V_{CE} = 5 V



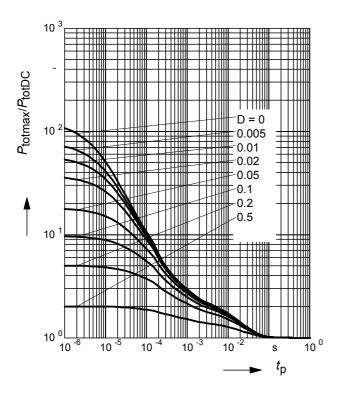
Permissible Pulse Load $R_{\text{thJS}} = f(t_p)$



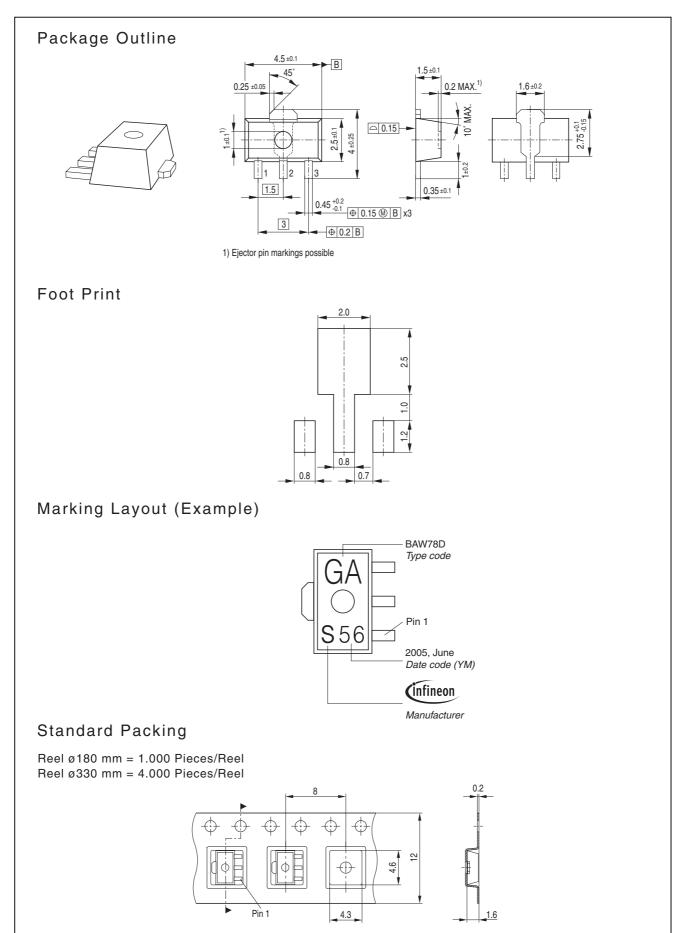


Permissible Pulse Load

 $P_{\text{totmax}}/P_{\text{totDC}} = f(t_{p})$











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